

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Patent Application of

TOHDA

Atty. Ref.: 925-222

Serial No. unknown

Group:

Filed: January 28, 2002

Examiner:

For: SEMICONDUCTOR DEVICE AND PROCESS FOR MANUFACTURING THE
SAME

* * * * *

January 28, 2002

Assistant Commissioner for Patents
Washington, DC 20231

Sir:

PRELIMINARY AMENDMENT

In order to place the above-identified application in better condition for
examination, please amend the application as follows:

IN THE CLAIMS

Please substitute the following amended claims for corresponding claims
previously presented. A copy of the amended claims showing current revisions is
attached.

5. The semiconductor device according to claim 1, wherein a height or a depth of the convex concave region formed on the upper surface of the ferroelectric layer is half or smaller than the thickness of the ferroelectric layer, and is in a range from the same as to half the thickness of the upper electrode layer.


6. The semiconductor device according to claim 1, wherein a height or a depth of the convex or concave region formed on the upper surface of the ferroelectric layer is half or smaller than the thickness of the ferroelectric layer, and is in a range from the same as to half the thickness of the upper electrode layer, and a height or a depth of the convex or concave region formed on the upper surface of the lower electrode layer is half or smaller than the thickness of the lower electrode layer, and is in a range from the same as to half the thickness of the ferroelectric layer.

REMARKS

Attached hereto is a marked-up version of the changes made to the claims by the current amendment. The attached page(s) is captioned "**Version With Markings To Show Changes Made.**"

Respectfully submitted,

NIXON & VANDERHYE P.C.

By: 
H. Warren Burnam, Jr.
Reg. No. 29,366

HWB:ecb
1100 North Glebe Road, 8th Floor
Arlington, VA 22201-4714
Telephone: (703) 816-4000
Facsimile: (703) 816-4100

VERSION WITH MARKINGS TO SHOW CHANGES MADE

IN THE CLAIMS

5. The semiconductor device according to claim 1-~~or~~2, wherein a height or a depth of the convex concave region formed on the upper surface of the ferroelectric layer is half or smaller than the thickness of the ferroelectric layer, and is in a range from the same as to half the thickness of the upper electrode layer.

6. The semiconductor device according to claim 1-~~or~~2, wherein a height or a depth of the convex or concave region formed on the upper surface of the ferroelectric layer is half or smaller than the thickness of the ferroelectric layer, and is in a range from the same as to half the thickness of the upper electrode layer, and a height or a depth of the convex or concave region formed on the upper surface of the lower electrode layer is half or smaller than the thickness of the lower electrode layer, and is in a range from the same as to half the thickness of the ferroelectric layer.